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IN THE SPECIFICATION

The paragraph at page 3, lines 5-6 is amended as follows:

D1

[Figure 1 is an illustration of a cross-sectional view of one embodiment of a contact structure] Figures 1, 1A are illustrations of a cross-sectional view of embodiments of a contact structure.

The paragraph beginning at page 4, line 13 is amended as follows:

Figure 1 is an illustration of one embodiment of contact structure 100 coupling device 103 to device 105 in integrated circuit 107. Contact structure 100 provides a conductive path for transmitting an electrical signal between devices 103 and 105. Contact structure 100, in one embodiment, includes polysilicon layer 109, barrier layers 111 and 113, and barrier structure

D2

115. Devices 103 and 105, which are coupled together by contact structure 100, are not limited to a particular type of device. Devices 103 and 105 may be any type of active or passive device capable of being fabricated using integrated circuit technologies, such as metal-oxide semiconductor (MOS) or bipolar technologies. In the example embodiment shown in Figure 1, device 103 is a capacitor and device 105 is a metal-oxide semiconductor field effect transistor (MOSFET). In the example embodiment shown in Figure 1A, device 103 is a capacitor and device 105A is a bipolar transistor (BJT). However, contact structure 100 is not limited to use in connection with a particular type of integrated circuit 107. Contact structure 100 is suitable for use in connection with linear integrated circuits, such as operational amplifiers, digital integrated circuits, such as boolean logic circuits and storage circuits, and memory circuits, such as dynamic random access memory (DRAM) circuits, static random access memory (SRAM) circuits, erasable programmable read only memory (EPROM) circuits, electrically erasable programmable read only memory (EEPROM) circuits, and flash memory circuits.